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Diodes Incorporated DMN65D8LW-7

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Datasheet of DMN65D8LW-7 - MOSFET N-CH 60V 0.3A SOT323

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DMN65D8LW

#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Package	I <sub>D</sub> T <sub>A</sub> = +25°C	
60V	3Ω @ V <sub>GS</sub> = 10V	SOT323	300mA	
607	4Ω @ V <sub>GS</sub> = 5V	301323	260mA	

### **Description**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

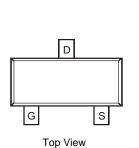
#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1KV (HBM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
   Qualified to AEC-Q101 Standards for High Reliability

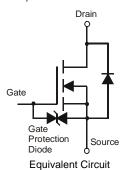
#### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)





Pin Configuration



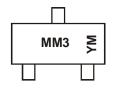
#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN65D8LW-7	SOT323	3000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



MM3 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

Year	2011	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α		3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	60	V		
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Ι <sub>D</sub>	300 230	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ΙD	260 210	mA
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	800	mA		
Maximum Body Diode Continuous Current (Note 6)	I <sub>S</sub>	1	Α		

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	ם	300	mW	
Total Power Dissipation	(Note 6)	$P_{D}$	432	IIIVV	
Thermal Decistores, Junction to Ambient	(Note 5)	1	398		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	290	°C/W	
Thermal Resistance, Junction to Case	(Note 5)	$R_{ heta JC}$	142		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

# **Electrical Characteristics** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	I <sub>GSS</sub>			±5.0	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1.2	_	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
Static Drain-Source On-Resistance	D (-)	l	2	3	Ω	$V_{GS} = 10V, I_D = 0.115A$
Static Drain-Source On-Nesistance	R <sub>DS</sub> (ON)		2.5	4	Ω	$V_{GS} = 5V, I_D = 0.115A$
Forward Transconductance	g <sub>FS</sub>	80	290	_	mS	$V_{DS} = 10V, I_D = 0.115A$
Diode Forward Voltage	$V_{SD}$	-	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>		22.0	_		
Output Capacitance	Coss		3.2	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>		2.0	_		
Gate Resistance	R <sub>G</sub>		79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge V <sub>GS</sub> = 10V	$Q_g$		0.87	_		
Total Gate Charge V <sub>GS</sub> = 4.5V	$Q_g$	_	0.43	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$
Gate-Source Charge	$Q_{gs}$	_	0.11	_	iiC	I <sub>D</sub> = 150mA
Gate-Drain Charge	$Q_{gd}$	_	0.11	_		
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.7	_		
Turn-On Rise Time	t <sub>r</sub>	_	2.8	_	nS	$V_{DD} = 30V$ , $I_D = 0.115A$ , $V_{GEN} = 10V$ ,
Turn-Off Delay Time	t <sub>D(off)</sub>	_	12.6	_	110	$R_{GEN} = 25\Omega$
Turn-Off Fall Time	t <sub>f</sub>		7.3	_		

Notes:

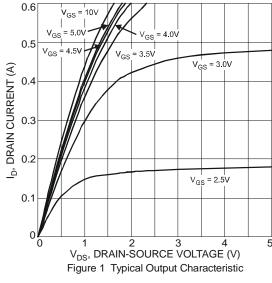
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
  7 .Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.

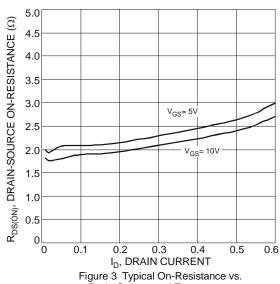
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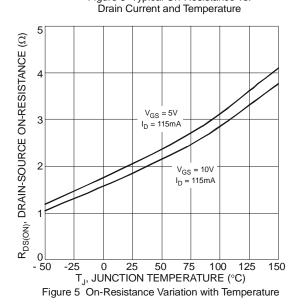
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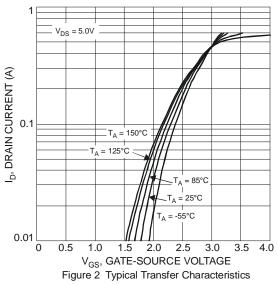


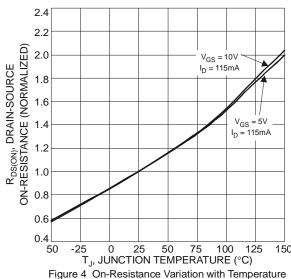
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2.0 1.8  $V_{GS(th)}$ , GATE THRESHOLD VOLTAGE (V) 1.6 I<sub>D</sub> = 1mA 1.2 = 250µA 1.0 0.8 0.6 0.4 0.2 50 75 100  $\mathsf{T}_\mathsf{J}$ , JUNCTION TEMPERATURE (°C)

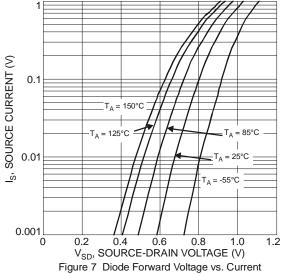
Figure 6 Gate Threshold Variation vs. Ambient Temperature

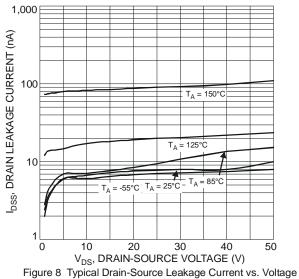
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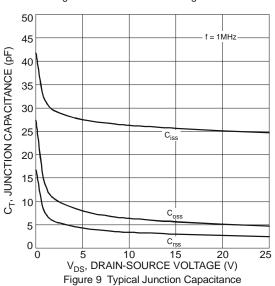
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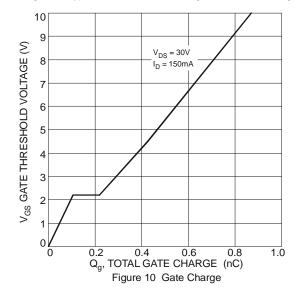


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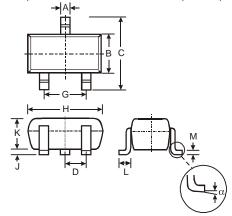






#### **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



301323						
Dim	Min	Max	Тур			
Α	0.25	0.40	0.30			
В	1.15	1.35	1.30			
C	2.00	2.20	2.10			
D	-	-	0.65			
G	1.20	1.40	1.30			
Н	1.80	2.20	2.15			
J	0.0	0.10	0.05			
K	0.90	1.00	1.00			
L	0.25	0.40	0.30			
М	0.10	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

SOT323

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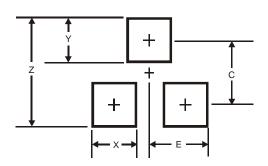
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#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0

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